SMD Switching Diode

COMCHIP
SMD Diodes Specialist

CDST226-G

RoHS Device

Features

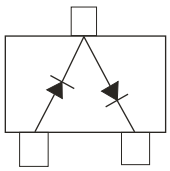
-Power dissipation: 150mW (@T_A=25 °C)

Mechanical data

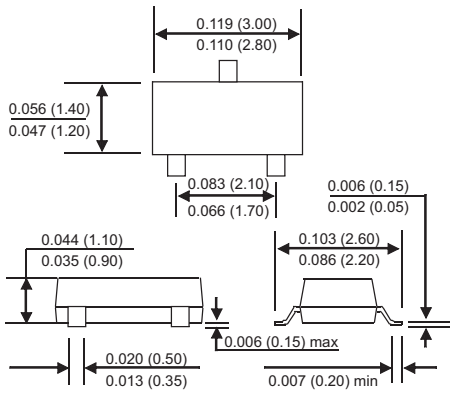
Case: SOT-23

Terminals: Solder plated, solderable per MIL-STD-750, Method 2026.

Marking: C3



SOT-23



Dimensions in inches and (millimeters)

Maximum Rating (at T_A=25 °C unless otherwise noted)

Parameter	Symbol	Limits	Unit
Non-Repetitive peak reverse voltage	V_{RM}	85	V
Peak repetitive peak reverse voltage Working peak reverse voltage DC blocking voltage	V_{RRM} V_{RWM} V_R	80	V
Forward continuous current	I_{FM}	300	mA
Average rectified output current	I_O	100	mA
Peak forward surge current @10mS	I_{FSM}	2	A
Power dissipation	P_D	150	mW
Storage temperature range	T_{STG}	-55 ~ +125	°C

Electrical Characteristics (at T_A=25 °C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Max	Unit
Reverse breakdown voltage	V_{BR}	I_R=100μA	80		V
Reverse leakage current	I_R	V_R=80V		0.5	μA
Forward voltage	V_F	I_F=100mA		1.2	V
Diode capacitance	C_T	V_R=0V, f=1MHz		3	pF
Reverse recovery time	t_{rr}			4	nS

Electrical and Characteristic Curves (CDST226-G)

Fig. 1 - Forward Characteristics

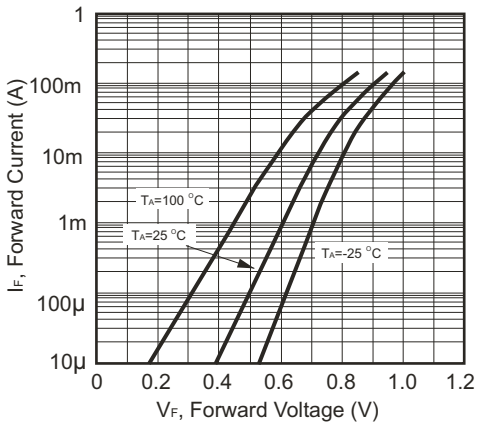


Fig. 2 - Reverse Characteristics

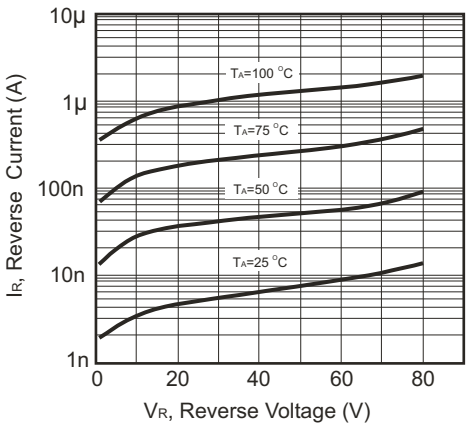


Fig. 3 - Diode Capacitance

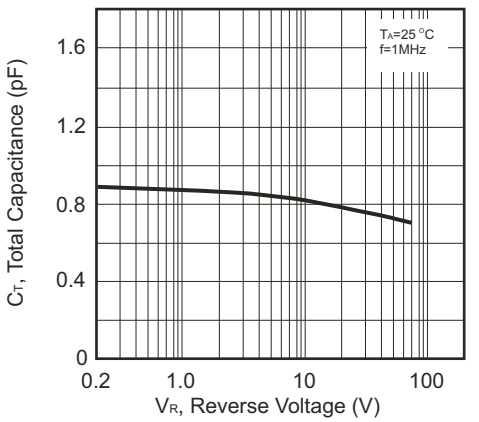


Fig. 4 - Reverse Recovery Characteristics

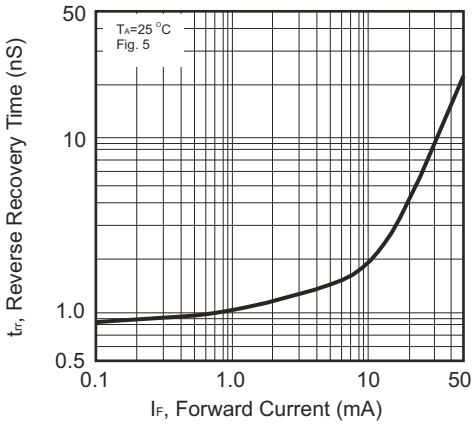


Fig. 5 - Reverse Recovery Time (trr) Test Circuit